



SANYO Semiconductors

# DATA SHEET

An ON Semiconductor Company

## EMH2409 — N-Channel Silicon MOSFET General-Purpose Switching Device Applications

### Features

- The EMH2409 incorporates a N-channel MOSFET that feature low ON-resistance and ultrahigh-speed switching, thereby enabling high-density mounting
- 4V drive
- Halogen free compliance
- Protection diode in

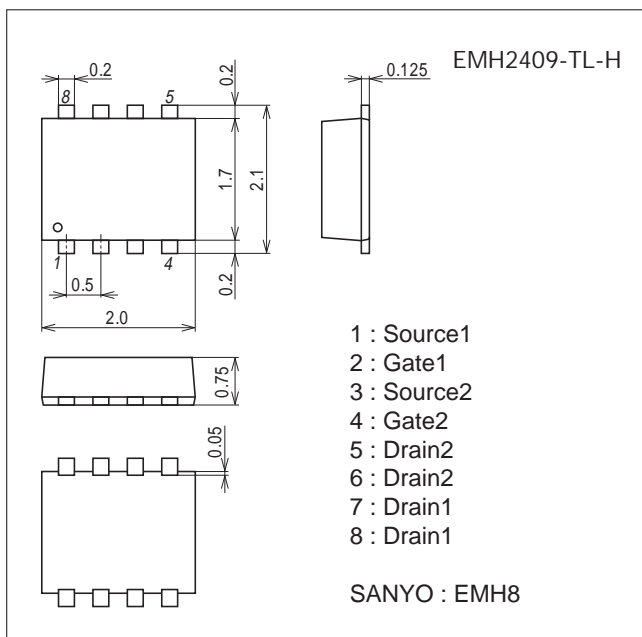
### Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		4	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycles≤1%	16	A
Allowable Power Dissipation	P <sub>D</sub>	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm) 1unit	1.0	W
Total Dissipation	P <sub>T</sub>	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1.2	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

### Package Dimensions

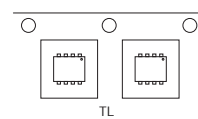
unit : mm (typ)  
7045-006



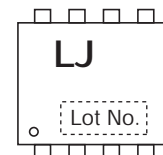
### Product & Package Information

- Package : EMH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

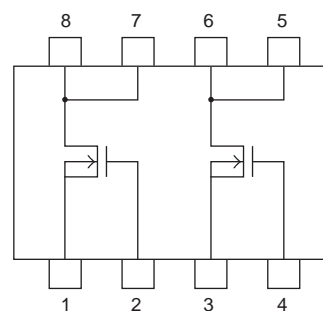
Packing Type : TL



Marking



### Electrical Connection

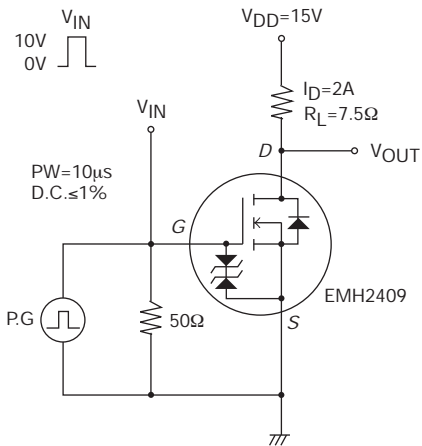


# EMH2409

## Electrical Characteristics at Ta=25°C

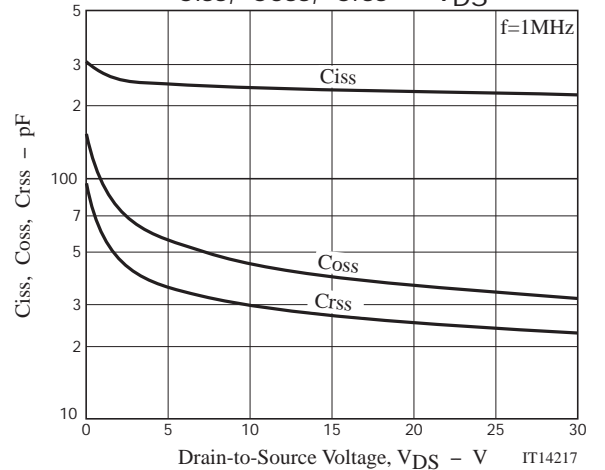
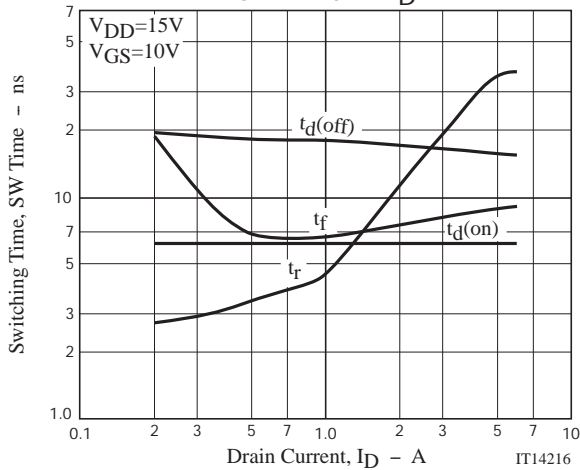
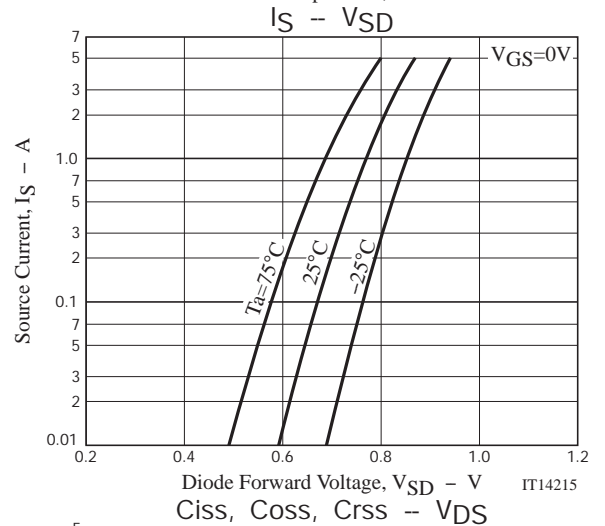
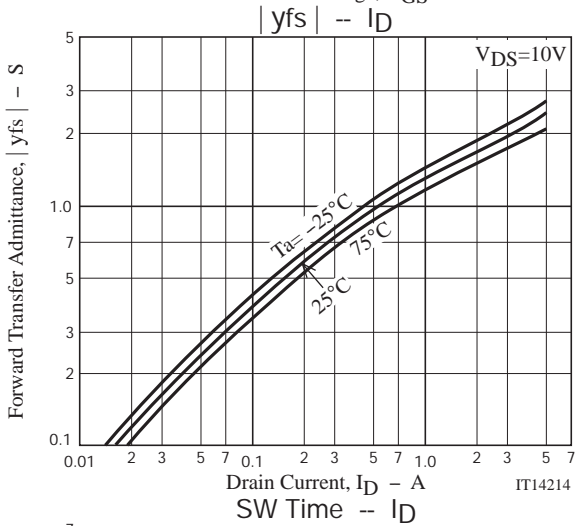
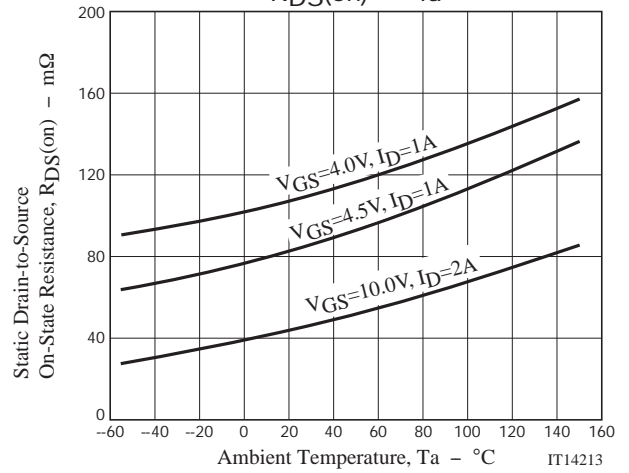
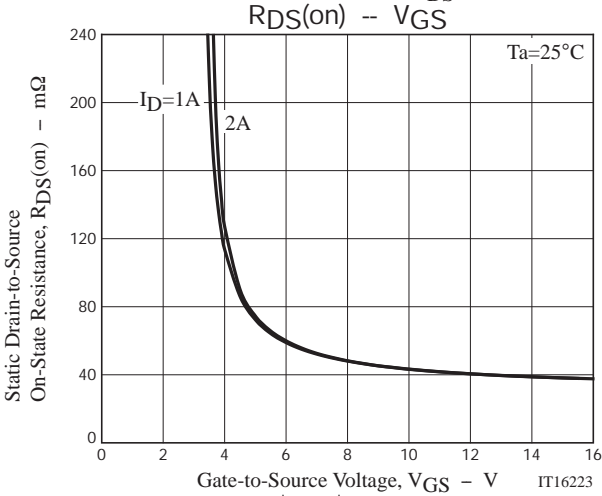
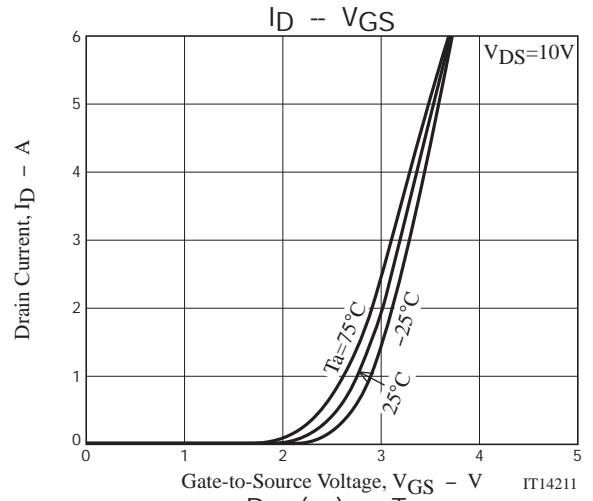
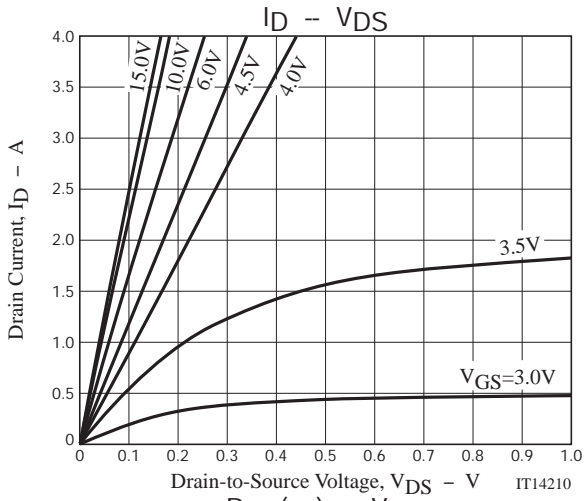
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =2A		1.66		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =2A, V <sub>GS</sub> =10V		45	59	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =1A, V <sub>GS</sub> =4.5V		85	119	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =1A, V <sub>GS</sub> =4V		110	155	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, f=1MHz		240		pF
Output Capacitance	C <sub>oss</sub>			45		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			30		pF
Turn-ON Delay Time	t <sub>d(on)</sub>		See specified Test Circuit.		6.2	
Rise Time	t <sub>r</sub>			11		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>			17		ns
Fall Time	t <sub>f</sub>			7.5		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =4A			4.4	
Gate-to-Source Charge	Q <sub>gs</sub>			1.1		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>			0.64		nC
Diode Forward Voltage	V <sub>SD</sub>		I <sub>S</sub> =4A, V <sub>GS</sub> =0V		0.82	1.2

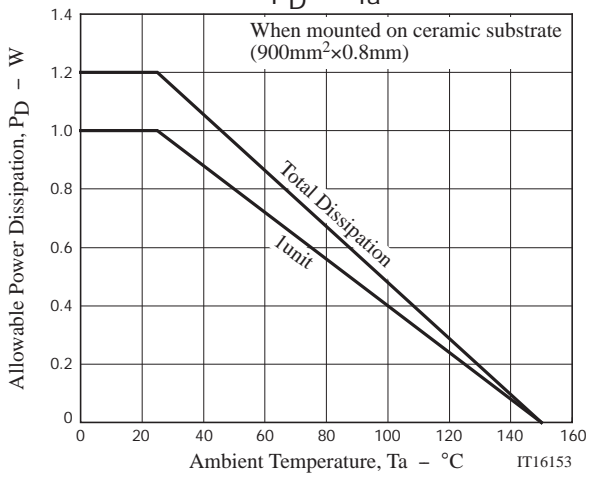
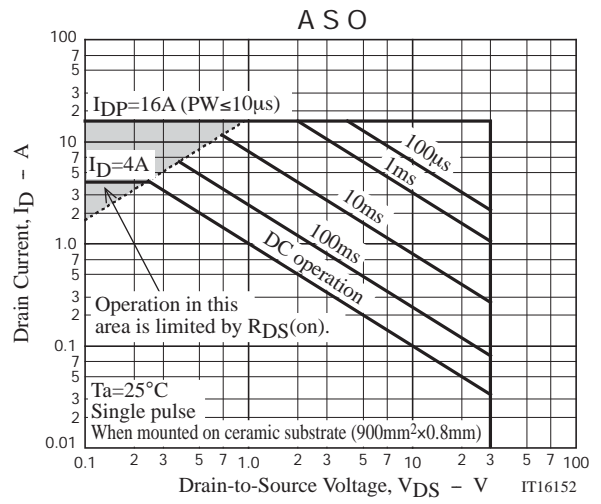
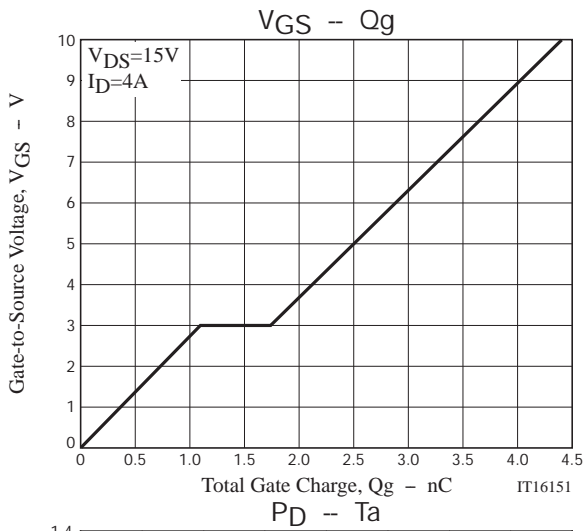
## Switching Time Test Circuit



## Ordering Information

Device	Package	Shipping	memo
EMH2409-TL-H	EMH8	3,000pcs./reel	Pb Free and Halogen Free





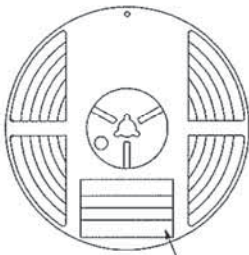
Embossed Taping Specification

EMH2409-TL-H

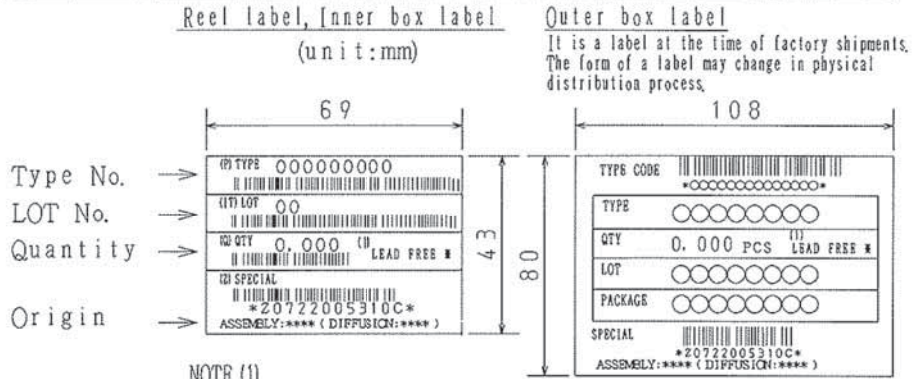
1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
EMH8	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



Reel label



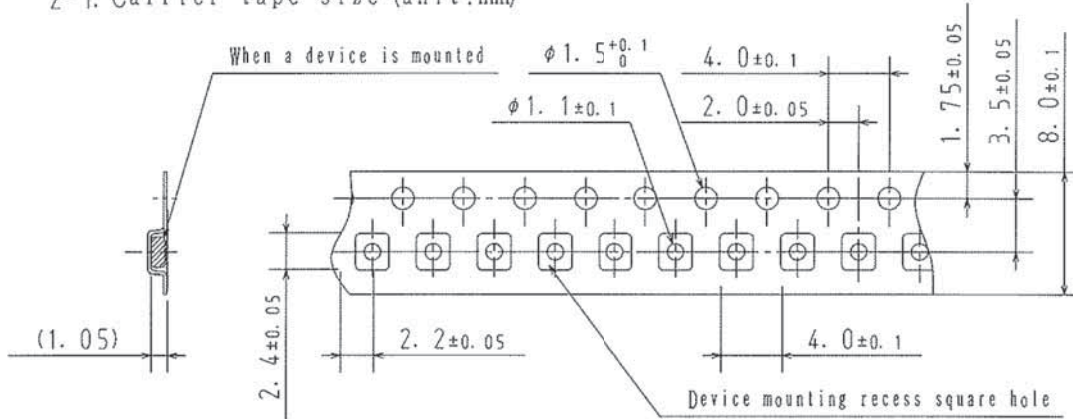
NOTE (1)

The LEAD FREE \* description shows that the surface treatment of the terminal is lead free.

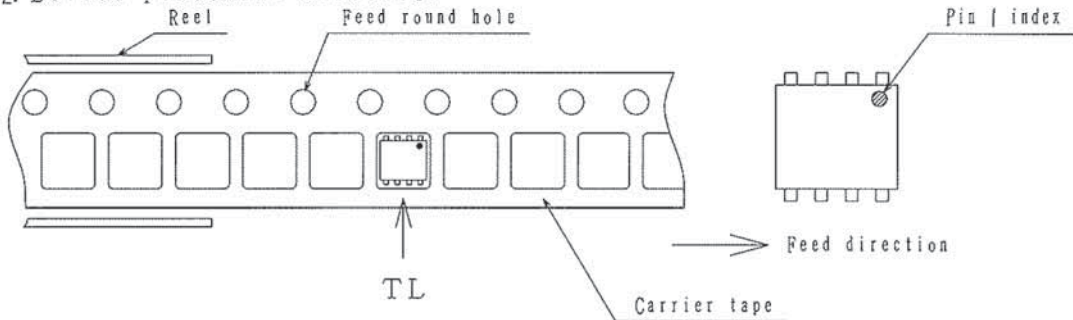
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction



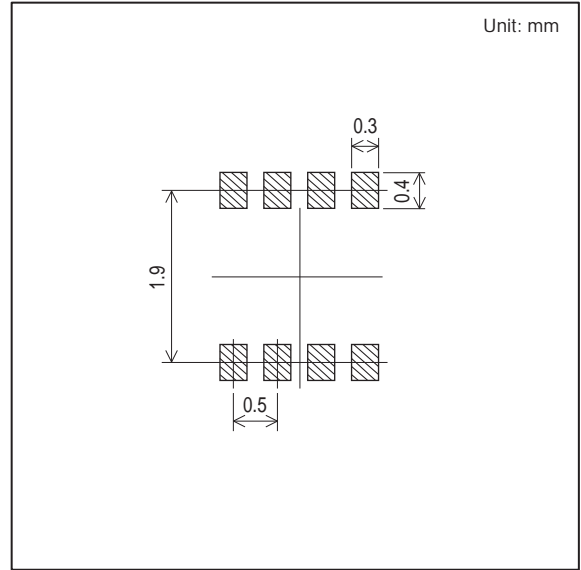
Those with pin | index on the feed hole side.....TL

# EMH2409

## Outline Drawing EMH2409-TL-H



## Land Pattern Example



Note on usage : Since the EMH2409 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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